

International IR Rectifier

PD -95674

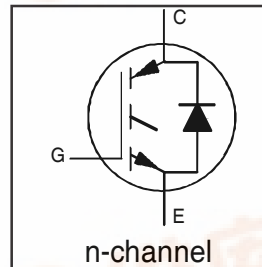
IRG4BC30KD-SPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST
SOFT RECOVERY DIODE

Short Circuit Rated
UltraFast IGBT

Features

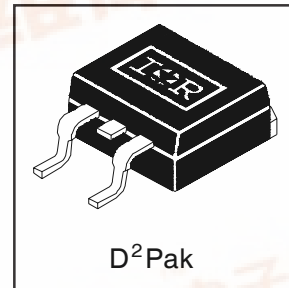
- High short circuit rating optimized for motor control, $t_{sc} = 10\mu s$, @360V $V_{CE} (start)$, $T_J = 125^\circ C$, $V_{GE} = 15V$
- Combines low conduction losses with high switching speed
- tighter parameter distribution and higher efficiency than previous generations
- IGBT co-packaged with HEXFRED™ ultrafast, ultrasoft recovery antiparallel diodes
- Lead-Free



$V_{CES} = 600V$
 $V_{CE(on)} \text{ typ.} = 2.21V$
@ $V_{GE} = 15V$, $I_C = 16A$

Benefits

- Latest generation 4 IGBTs offer highest power density motor controls possible
- HEXFRED™ diodes optimized for performance with IGBTs. Minimized recovery characteristic reduce noise, EMI and switching losses
- This part replaces the IRGBC30KD2-S and IRGBC30MD2-S products
- For hints see design tip 97003



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Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	28	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	16	
I_{CM}	Pulsed Collector Current ①	58	
I_{LM}	Clamped Inductive Load Current ②	58	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	12	
I_{FM}	Diode Maximum Forward Current	58	μs
t_{sc}	Short Circuit Withstand Time	10	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	100	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	42	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	1.2	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	—	2.5	
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.5	—	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted, steady-state) ③	—	40	
Wt	Weight	1.44	—	g

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage ^③	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.54	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.21	2.7	V	$I_C = 16A, V_{GE} = 15V$
		—	2.88	—		$I_C = 28A, V_{GE} = 15V$
		—	2.36	—		$I_C = 16A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-12	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ^④	5.4	8.1	—	S	$V_{CE} = 100V, I_C = 16A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	2500		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
V_{FM}	Diode Forward Voltage Drop	—	1.4	1.7	V	$I_C = 12A$ See Fig. 13
		—	1.3	1.6		$I_C = 12A, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	67	100	nC	$I_C = 16A$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	11	16		$V_{CC} = 400V$ See Fig. 8
Q_{gc}	Gate - Collector Charge (turn-on)	—	25	37		$V_{GE} = 15V$
$t_{d(on)}$	Turn-On Delay Time	—	60	—	ns	$T_J = 25^\circ\text{C}$
t_r	Rise Time	—	42	—		$I_C = 16A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	—	160	250		$V_{GE} = 15V, R_G = 23\Omega$
t_f	Fall Time	—	80	120		Energy losses include "tail" and diode reverse recovery
E_{on}	Turn-On Switching Loss	—	0.60	—	mJ	See Fig. 9,10,14
E_{off}	Turn-Off Switching Loss	—	0.58	—		
E_{ts}	Total Switching Loss	—	1.18	1.6		
t_{sc}	Short Circuit Withstand Time	10	—	—	μs	$V_{CC} = 360V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 10\Omega, V_{CPK} < 500V$
$t_{d(on)}$	Turn-On Delay Time	—	58	—	ns	$T_J = 150^\circ\text{C}$ See Fig. 11,14
t_r	Rise Time	—	42	—		$I_C = 16A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	—	210	—		$V_{GE} = 15V, R_G = 23\Omega$
t_f	Fall Time	—	160	—		Energy losses include "tail" and diode reverse recovery
E_{ts}	Total Switching Loss	—	1.69	—	mJ	
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	920	—	pF	$V_{GE} = 0V$
C_{oes}	Output Capacitance	—	110	—		$V_{CC} = 30V$ See Fig. 7
C_{res}	Reverse Transfer Capacitance	—	27	—		$f = 1.0MHz$
t_{rr}	Diode Reverse Recovery Time	—	42	60	ns	$T_J = 25^\circ\text{C}$ See Fig. 14
		—	80	120		$T_J = 125^\circ\text{C}$
I_{rr}	Diode Peak Reverse Recovery Current	—	3.5	6.0	A	$T_J = 25^\circ\text{C}$ See Fig. 15
		—	5.6	10		$T_J = 125^\circ\text{C}$
Q_{rr}	Diode Reverse Recovery Charge	—	80	180	nC	$T_J = 25^\circ\text{C}$ See Fig. 16
		—	220	600		$T_J = 125^\circ\text{C}$
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During t_b	—	180	—	A/ μs	$T_J = 25^\circ\text{C}$ See Fig. 17
		—	160	—		$T_J = 125^\circ\text{C}$

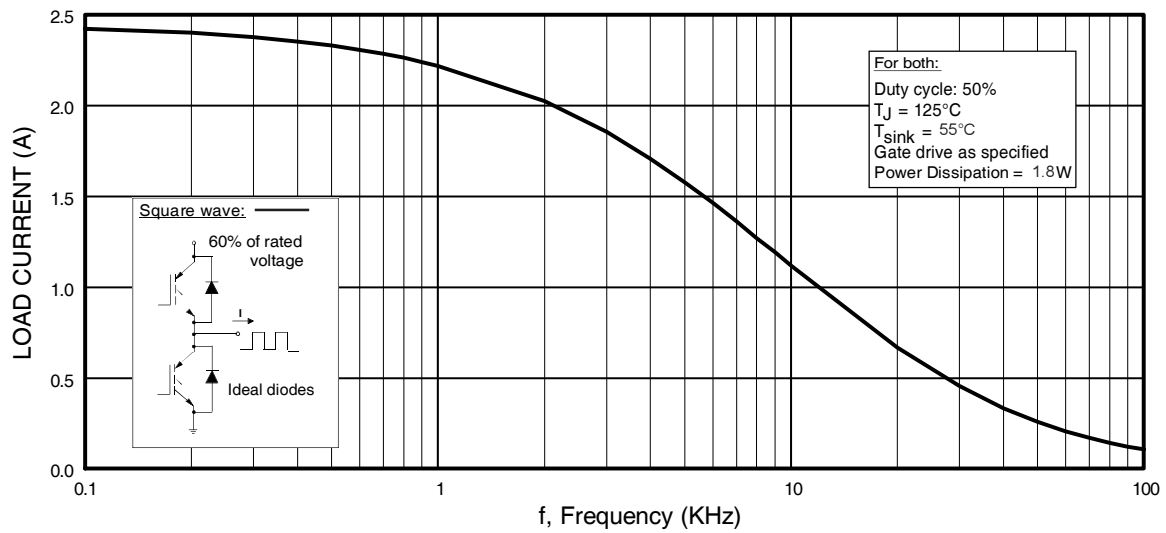


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

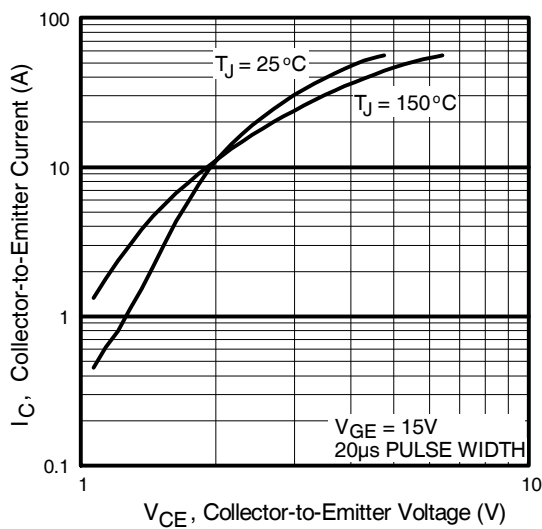


Fig. 2 - Typical Output Characteristics

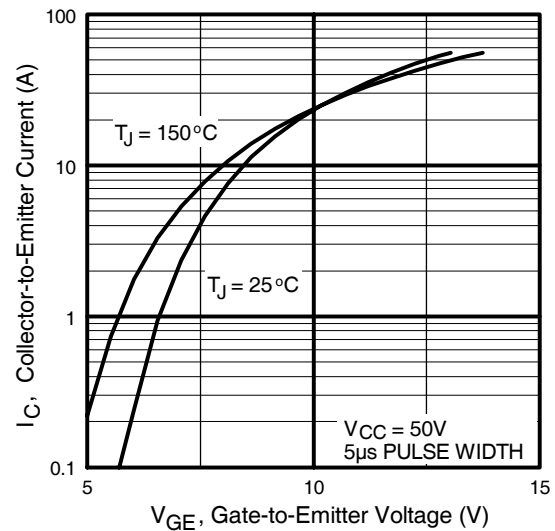


Fig. 3 - Typical Transfer Characteristics

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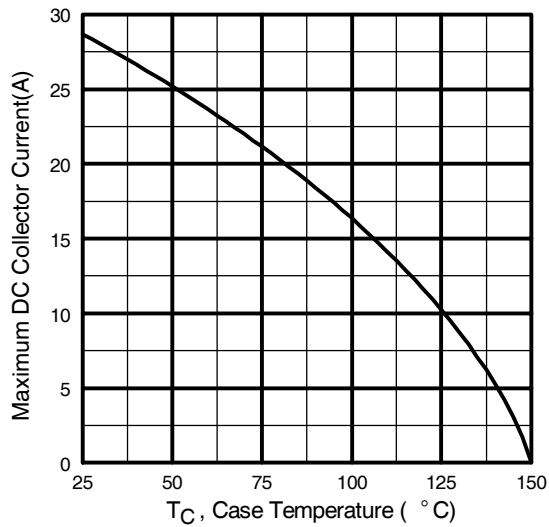


Fig. 4 - Maximum Collector Current vs. Case Temperature

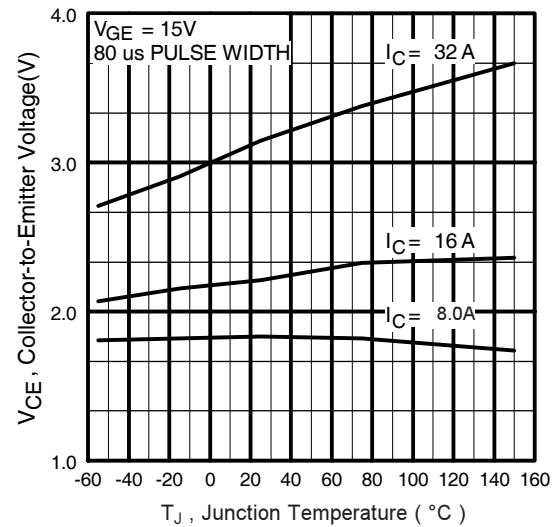


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

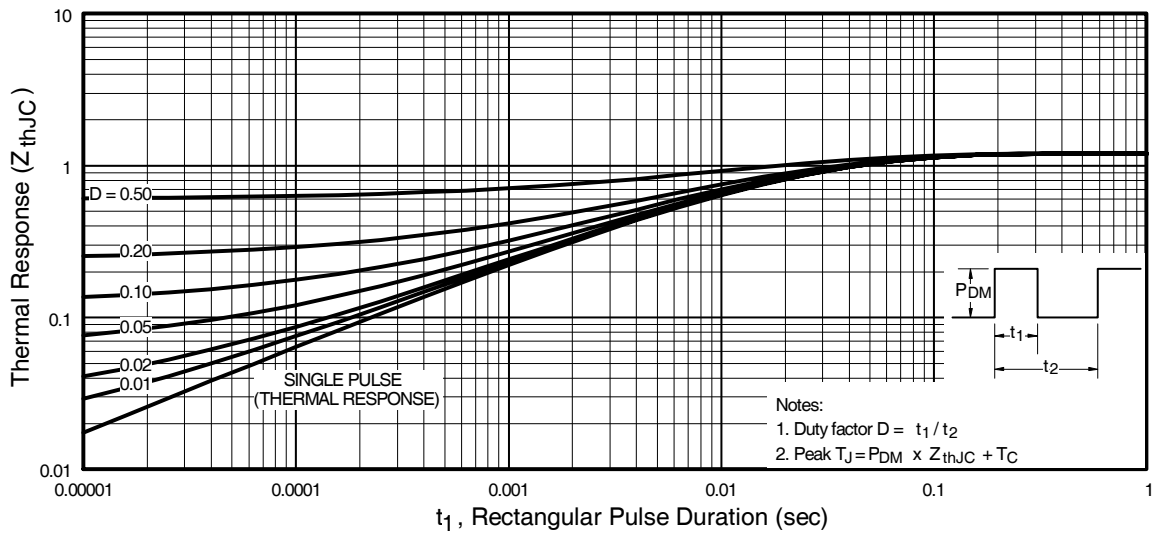


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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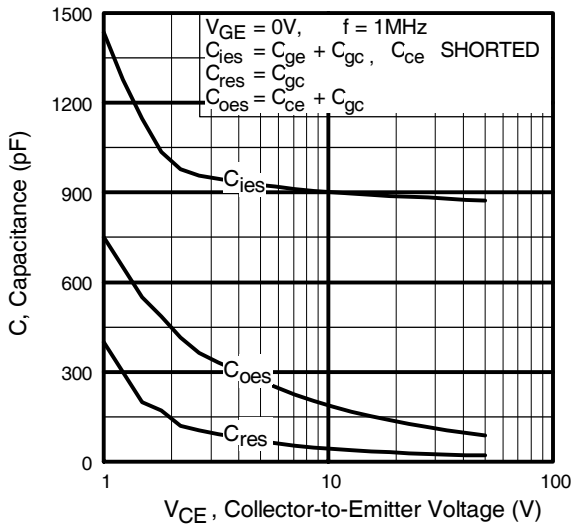


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

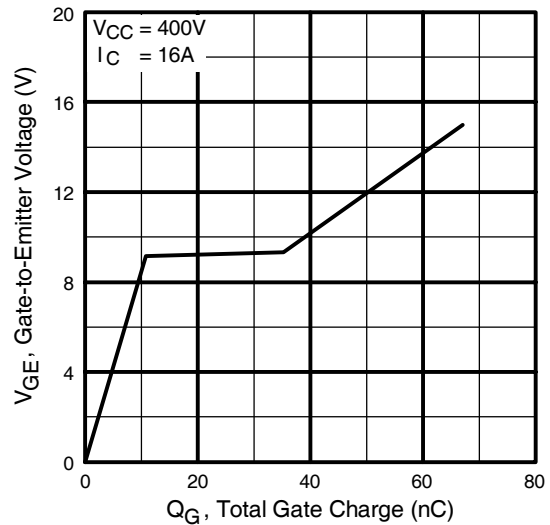


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

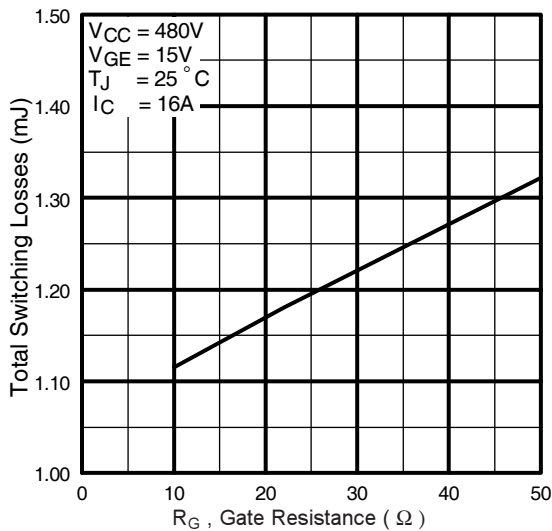


Fig. 9 - Typical Switching Losses vs. Gate Resistance

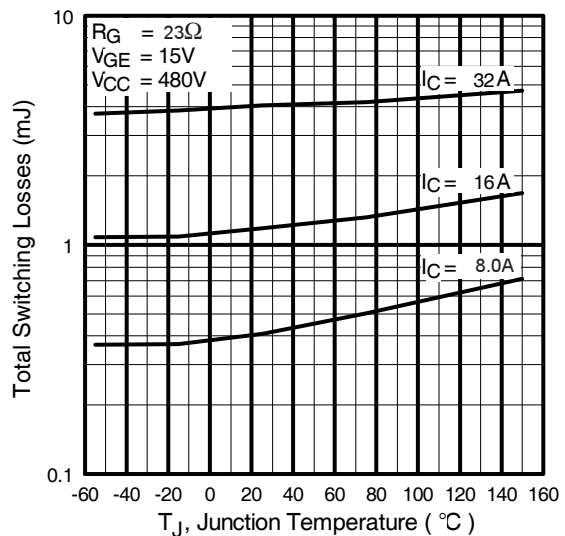


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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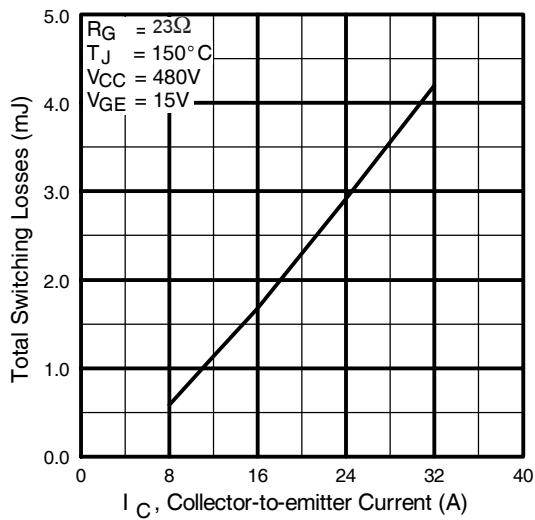


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

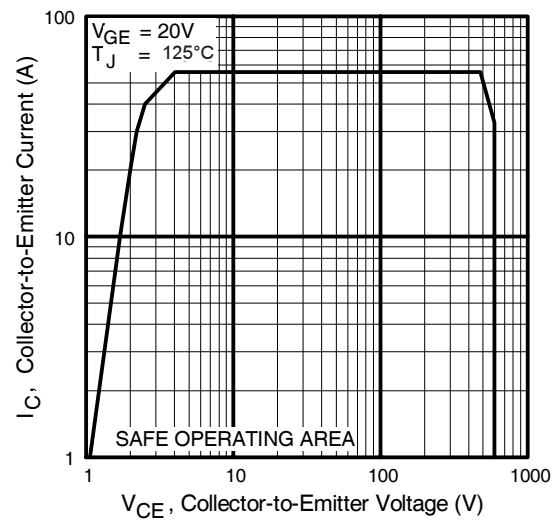


Fig. 12 - Turn-Off SOA

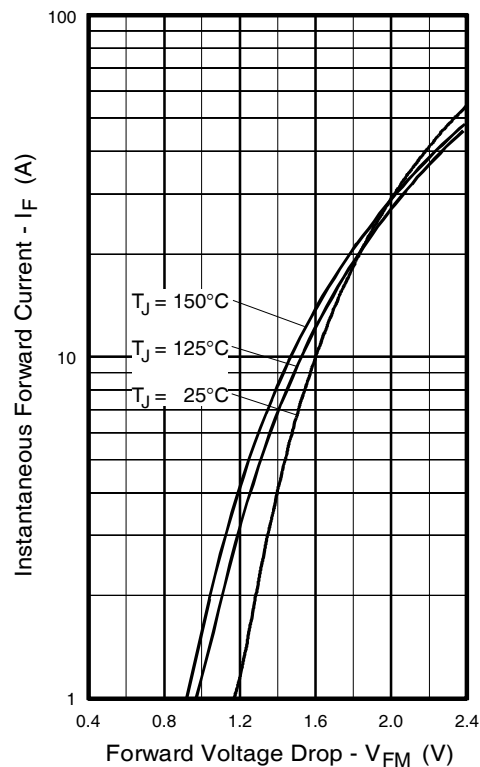


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

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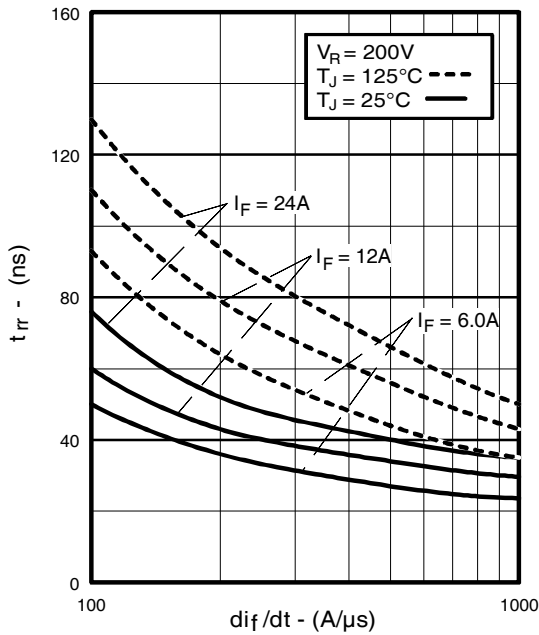


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

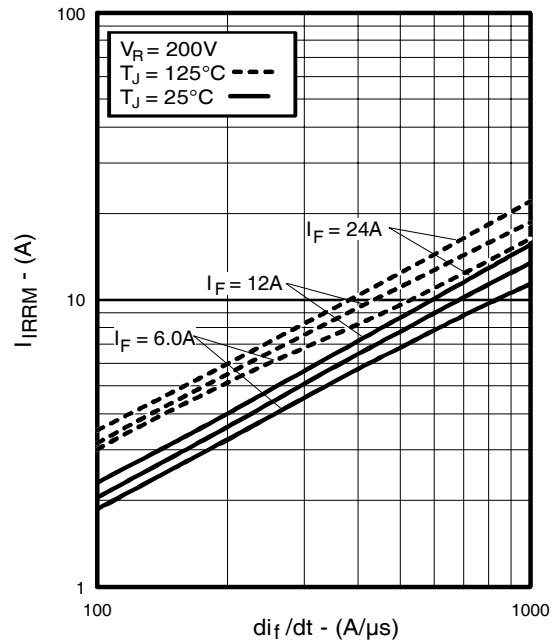


Fig. 15 - Typical Recovery Current vs. di_f/dt

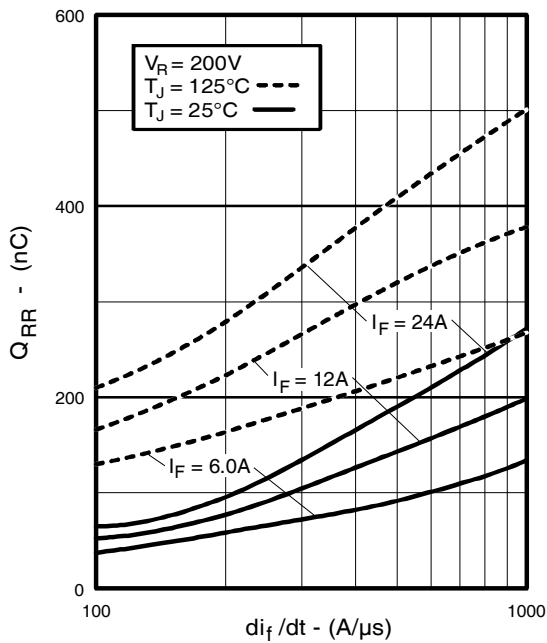


Fig. 16 - Typical Stored Charge vs. di_f/dt

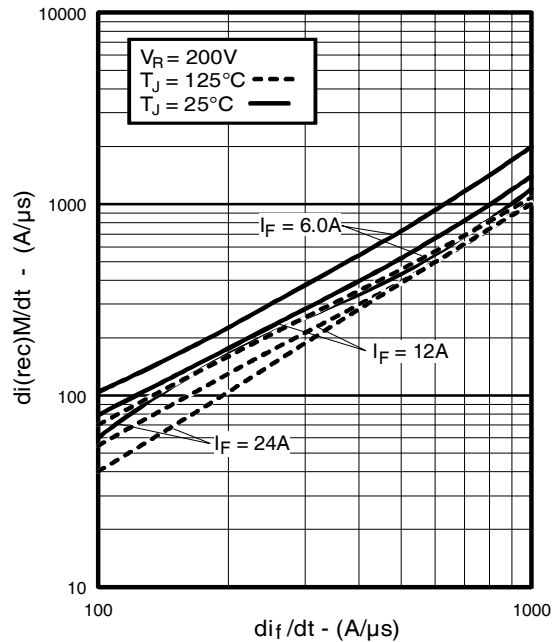


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

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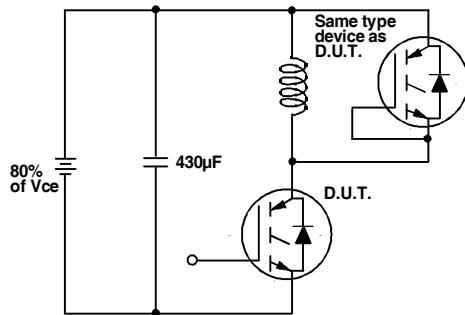


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

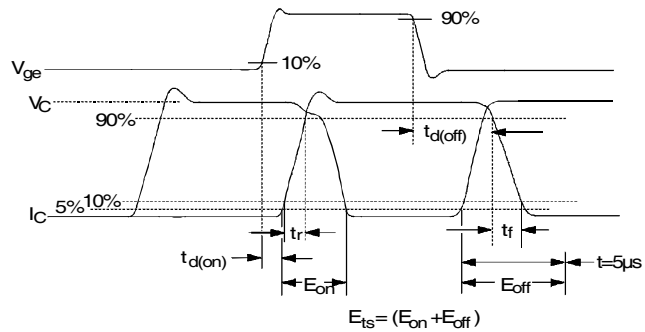


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

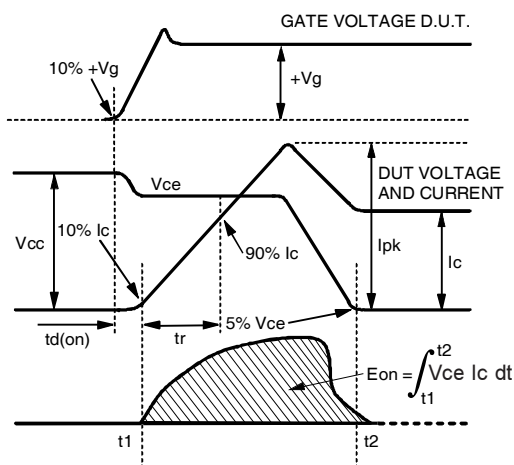


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

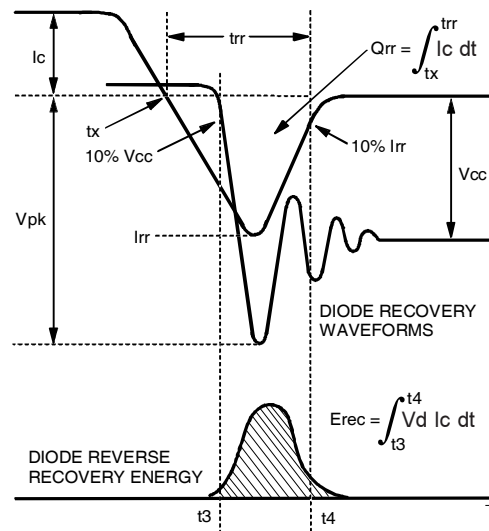
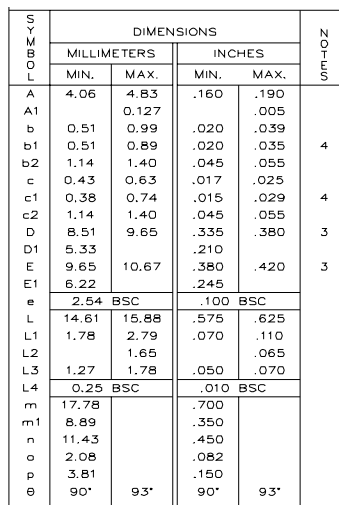


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

Dimensions are shown in millimeters (inches)



<u>HEXFET</u>	<u>IGBTs, CoPACK</u>	<u>DIODES</u>
1.- GATE	1.- GATE	1.- ANODE *
2.- DRAIN	2.- COLLECTOR	2.- CATHODE
3.- SOURCE	3.- EMITTER	3.- ANODE

* PART DEPENDENT.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

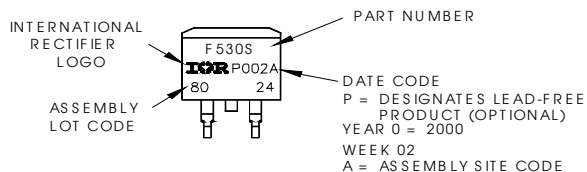
D²Pak Part Marking Information (Lead-Free)

Note: "P" in assembly line position indicates "Lead-Free"

Diagram illustrating the markings on a power MOSFET package:

- INTERNATIONAL RECTIFIER LOGO**: Points to the "IR" logo on the package.
- PART NUMBER**: Points to the "F 530S" marking.
- DATE CODE**: Points to the "002L" marking.
- YEAR 0 = 2000**: Explains the meaning of the first digit of the date code.
- WEEK 02**: Explains the meaning of the second digit of the date code.
- LINE L**: Explains the meaning of the letter of the date code.
- ASSEMBLY LOT CODE**: Points to the "80" and "24" markings.

OR



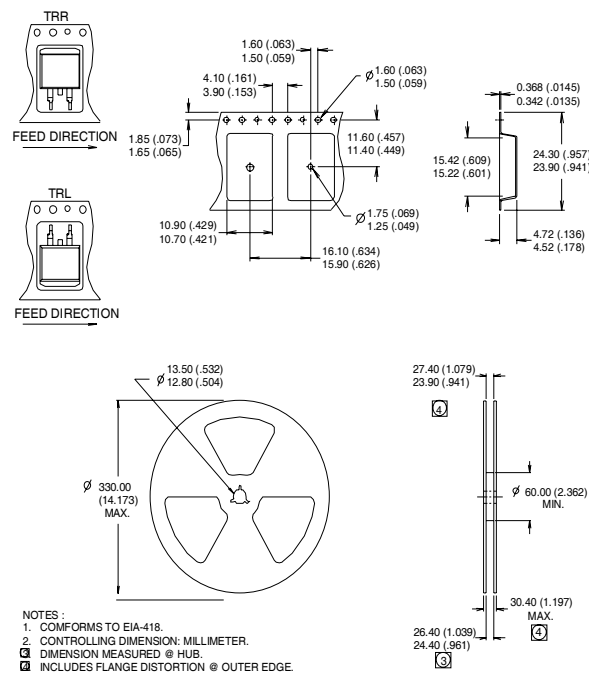
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Notes:

- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G=23\Omega$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width $5.0\mu s$, single shot.
- ⑤ When mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

D²Pak Tape & Reel Information



Data and specifications subject to change without notice.

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